AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (Currently Amended): A light source apparatus equipped with a GaN type semiconductor light emitting element, comprising

a GaN type semiconductor light emitting element;

a spatial filter for eliminating stray light from the light emitted from the GaN type semiconductor light emitting element, wherein

said stray light amounts to 20% or less of the total output of the light emitted from said GaN type semiconductor light emitting element when said GaN type semiconductor [[laser]] light emitting element is driven at the maximum output thereof.

2. (Original): A light source apparatus equipped with a GaN type semiconductor light emitting element as defined in claim 1, further comprising

a focusing optical system for focusing the light emitted from the GaN type semiconductor light emitting element, wherein

the spatial filter is formed of a slit panel or a pinhole panel disposed adjacent to the convergence position of the light focused by the focusing optical system.

3. (Original): A light source apparatus equipped with a GaN type semiconductor light emitting element as defined in claim 1, further comprising

a focusing optical system for focusing the light emitted from the GaN type semiconductor light emitting element, wherein

the spatial filter is formed of a partially reflective mirror that partially reflects the light near the convergence position of the light focused by the focusing optical system.

4. (Currently Amended): A light source apparatus equipped with a GaN type semiconductor light emitting element as defined in claim 1, wherein

the spatial filter is a polarization element that eliminates the light components other than the TE mode components of the light emitted from the GaN type semiconductor [[laser]] light emitting element.

5. (Previously Presented): A light source apparatus equipped with a GaN type semiconductor light emitting element as defined in claim 1, wherein

the stray light is stray light that is generated when the drive current of the GaN type semiconductor light emitting element is less than the laser oscillation threshold value.

6. (Currently Amended): A method of eliminating stray light comprising the step of

emitting light from a GaN type semiconductor light emitting element;

eliminating, by use of a spatial filter, stray light from the light emitted from the light source apparatus equipped with [[a]] the GaN type semiconductor light emitting element; wherein

said stray light amounts to 20% or less of the total output of the light emitted from said GaN type semiconductor light emitting element when said GaN type semiconductor [[laser]] light emitting element is driven at the maximum output thereof.

7. (Original): A method of eliminating stray light as defined in claim 6, wherein

the stray light is stray light that is generated when the drive current of the GaN type semiconductor light emitting element is less than the laser oscillation threshold value.

8. (Currently Amended): A device as defined in any one of claims 1 to 5 and 10 to 12, further comprising an ~~An~~ image forming apparatus that scans a photosensitive material with a light modulated based on image data to form the image borne by said image data~~, wherein~~

~~the light source apparatus for emitting said light is the light source apparatus defined in any one of claims 1 to 5 and 10 to 12~~.

9. (Currently Amended): A device as defined in claim 5, further comprising an ~~An~~ image forming apparatus that scans a photosensitive material with a light modulated based on image data to form the image borne by said image data~~, wherein~~

~~the light source apparatus for emitting said light is the light source apparatus defined in claim 5~~.

10. (Previously Presented): A light source apparatus equipped with a GaN type semiconductor light emitting element as defined in claim 2, wherein

the stray light is stray light that is generated when the drive current of the GaN type semiconductor light emitting element is less than the laser oscillation threshold value.

11. (Previously Presented): A light source apparatus equipped with a GaN type semiconductor light emitting element as defined in claim 3, wherein

the stray light is stray light that is generated when the drive current of the GaN type semiconductor light emitting element is less than the laser oscillation threshold value.

12. (Previously Presented): A light source apparatus equipped with a GaN type semiconductor light emitting element as defined in claim 4, wherein

the stray light is stray light that is generated when the drive current of the GaN type semiconductor light emitting element is less than the laser oscillation threshold value.

13. (Previously Presented): A light source apparatus equipped with a GaN type semiconductor light emitting element as defined in claim 2, wherein a slit width of the slit panel is less than or equal to twice a spot diameter of the light at the convergence position.

14. (Currently Amended): A method of eliminating stray light comprising the steps of

equipping a light source apparatus with a GaN type semiconductor light emitting element;

providing the light source with a spatial filter; and

eliminating, by use of the stray filter, stray light from the emitted light, wherein

the stray light amounts to 20% or less of the total output of the light emitted from the GaN type semiconductor light emitting element when the GaN type semiconductor [[laser]] light emitting element is driven at the maximum output thereof.

15. (Previously Presented): A method of eliminating stray light as defined in claim 14, wherein

the stray light is stray light that is generated when the drive current of the GaN type semiconductor light emitting element is less than the laser oscillation threshold value.

16. (Previously Presented): A light source apparatus equipped with a GaN type semiconductor light emitting element as defined in claim 1, wherein

the GaN type semiconductor light emitting element has an active layer having stripe portions, further wherein

the stray light is randomly polarized light emitted from portions of the semiconductor light emitting element other than the stripe portions of the active layer.

17. (Previously Presented): A light source apparatus equipped with a GaN type semiconductor light emitting element as defined in claim 16, wherein

the stray light includes light that leaks from the stripe portions of the active layer to portions other that the stripe portions.

18. (Previously Presented): A light source apparatus equipped with a GaN type semiconductor light emitting element as defined in claim 2, wherein

the GaN type semiconductor light emitting element has an active layer having stripe portions, further wherein

the stray light is randomly polarized light emitted from portions of the semiconductor light emitting element other than the stripe portions of the active layer, further wherein

the stray light is cutoff by the slit panel.